

Sheet 1 of 1

INFORMATION DISCLOSURE
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APPLICANT

NAKAMURA et al

FILING DATE

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May 1, 2000

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(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[Signature]</i>	6,172,382	01/2001	NAGAHAMA et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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JP 9-148678	06/1997	JAPAN			X

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

<i>[Signature]</i>	NAKAMURA et al., "Present Status of InGaN/GaN/AlGaN-Based Laser Diodes," Proceedings of the Second International Conference on Nitride Semiconductors (INCS '97), 1997, pp. 444-446
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<i>[Signature]</i>	NAKAMURA et al., "Room-temperature continuous-wave operation of InGaN multi-quantum-well structure laser diodes," Appl. Phys. Lett. 69(26) (Dec. 23, 1996), pp. 4056-4058

*Examiner

Date Considered

5/06

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